ABSTRACT OF THE DISCLOSURE

This invention relates to a negative photoresist composition with multi-reaction models. When the photoresist composition according to the present invention

5　is used in photolithography processes employing UV light to produce cross-link reactions and multi-reactions including radical polymerization and cationic polymerization also occur. The photoresist composition can be used to control light reaction efficiency and increase reaction

10　thoroughness, thus obtaining a high resolution pattern.